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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, LVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4125azi-s413

Contents

Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0+ CPU in the PSoC 4100S is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. Most instructions are 16 bits in length and the CPU executes a subset of the Thumb-2 instruction set. It includes a nested vectored interrupt controller (NVIC) block with eight interrupt inputs and also includes a Wakeup Interrupt Controller (WIC). The WIC can wake the processor from Deep Sleep mode, allowing power to be switched off to the main processor when the chip is in Deep Sleep mode.

The CPU also includes a debug interface, the serial wire debug (SWD) interface, which is a two-wire form of JTAG. The debug configuration used for PSoC 4100S has four breakpoint (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC 4100S device has a flash module with a flash accelerator, tightly coupled to the CPU to improve average access times from the flash block. The low-power flash block is designed to deliver two wait-state (WS) access time at 48 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average.

SRAM

Eight KB of SRAM are provided with zero wait-state access at 48 MHz.

SROM

An 8 KB supervisory ROM that contains boot and configuration routines is provided.

System Resources

Power System

The power system is described in detail in the section Power on page 11. It provides assurance that voltage levels are as required for each respective mode and either delays mode entry (for example, on power-on reset (POR)) until voltage levels are as required for proper functionality, or generates resets (for example, on brown-out detection). The PSoC 4100S operates with a single external supply over the range of either 1.8 V ±5% (externally regulated) or 1.8 to 5.5 V (internally regulated) and has three different power modes, transitions between which are managed by the power system. The PSoC 4100S provides Active, Sleep, and Deep Sleep low-power modes.

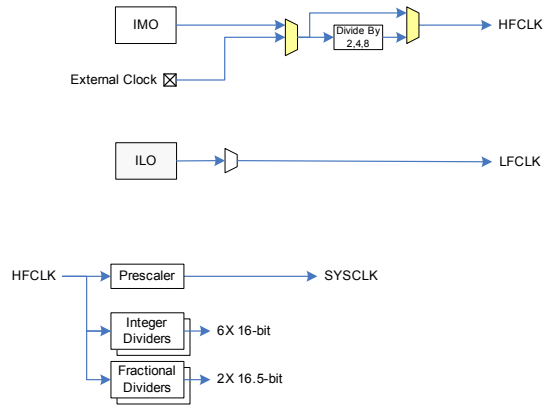
All subsystems are operational in Active mode. The CPU subsystem (CPU, flash, and SRAM) is clock-gated off in Sleep mode, while all peripherals and interrupts are active with instantaneous wake-up on a wake-up event. In Deep Sleep mode, the high-speed clock and associated circuitry is switched off; wake-up from this mode takes 35 µs. The opamps can remain operational in Deep Sleep mode.

Clock System

The PSoC 4100S clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that there are no metastable conditions.

The clock system for the PSoC 4100S consists of the internal main oscillator (IMO), internal low-frequency oscillator (ILO), a 32 kHz Watch Crystal Oscillator (WCO) and provision for an external clock. Clock dividers are provided to generate clocks for peripherals on a fine-grained basis. Fractional dividers are also provided to enable clocking of higher data rates for UARTs.

Figure 2. PSoC 4100S MCU Clocking Architecture



The HFCLK signal can be divided down to generate synchronous clocks for the analog and digital peripherals. There are eight clock dividers for the PSoC 4100S; two of those are fractional dividers. The 16-bit capability allows flexible generation of fine-grained frequency values and is fully supported in PSoC Creator

IMO Clock Source

The IMO is the primary source of internal clocking in the PSoC 4100S. It is trimmed during testing to achieve the specified accuracy.The IMO default frequency is 24 MHz and it can be adjusted from 24 to 48 MHz in steps of 4 MHz. The IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low power, nominally 40-kHz oscillator, which is primarily used to generate clocks for the watchdog timer (WDT) and peripheral operation in Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

Watch Crystal Oscillator (WCO)

The PSoC 4100S clock subsystem also implements a low-frequency (32-kHz watch crystal) oscillator that can be used for precision timing applications.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO; this allows watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the set timeout occurs. The watchdog reset is recorded in a Reset Cause register, which is firmware readable.

supports EZI2C that creates a mailbox address range in the memory of the PSoC 4100S and effectively reduces I^2C communication to reading from and writing to an array in memory. In addition, the block supports an 8-deep FIFO for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time.

The I^2C peripheral is compatible with the I^2C Standard-mode and Fast-mode devices as defined in the NXP I^2C-bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes.

The PSoC 4100S is not completely compliant with the I^2C spec in the following respect:

- GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I^2C system.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated.

SPI Mode: The SPI mode supports full Motorola SPI, TI SSP (adds a start pulse used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO.

GPIO

The PSoC 4100S has up to 36 GPIOs. The GPIO block implements the following:

- Eight drive modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes
- Selectable slew rates for dV/dt related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width (less for Ports 2 and 3). During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4100S).

Special Function Peripherals

CapSense

CapSense is supported in the PSoC 4100S through a CapSense Sigma-Delta (CSD) block that can be connected to any pins through an analog multiplex bus via analog switches. CapSense function can thus be provided on any available pin or group of pins in a system under software control. A PSoC Creator component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another analog multiplex bus to provide water-tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input. Proximity sensing can also be implemented.

The CapSense block has two IDACs, which can be used for general purposes if CapSense is not being used (both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).

The CapSense block also provides a 10-bit Slope ADC function which can be used in conjunction with the CapSense function.

The CapSense block is an advanced, low-noise, programmable block with programmable voltage references and current source ranges for improved sensitivity and flexibility. It can also use an external reference voltage. It has a full-wave CSD mode that alternates sensing to VDDA and ground to null out power-supply related noise.

LCD Segment Drive

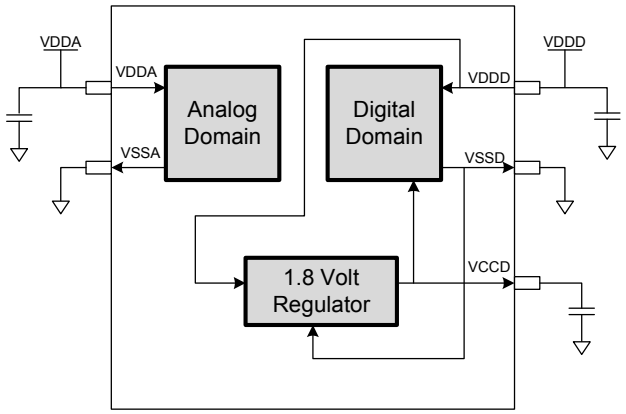
The PSoC 4100S has an LCD controller, which can drive up to 4 commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as Digital Correlation and PWM. Digital Correlation pertains to modulating the frequency and drive levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal to zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays. PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).

Port/Pin	Analog	Smart I/O	Alternate Function 1	Alternate Function 2	Alternate Function 3	Deep Sleep 1	Deep Sleep 2
P2.4	sarmux[4]	prgio[0].io[4]	tcpwm.line[0]:1				scb[1].spi_select1:1
P2.5	sarmux[5]	prgio[0].io[5]	tcpwm.line_compl[0]:1				scb[1].spi_select2:1
P2.6	sarmux[6]	prgio[0].io[6]	tcpwm.line[1]:1				scb[1].spi_select3:1
P2.7	sarmux[7]	prgio[0].io[7]	tcpwm.line_compl[1]:1			lpcomp.comp[0]:1	scb[2].spi_mosi
P3.0		prgio[1].io[0]	tcpwm.line[0]:0	scb[1].uart_rx:1		scb[1].i2c_scl:2	scb[1].spi_mosi:0
P3.1		prgio[1].io[1]	tcpwm.line_compl[0]:0	scb[1].uart_tx:1		scb[1].i2c_sda:2	scb[1].spi_miso:0
P3.2		prgio[1].io[2]	tcpwm.line[1]:0	scb[1].uart_cts:1		cpuss.swd_data	scb[1].spi_clk:0
P3.3		prgio[1].io[3]	tcpwm.line_compl[1]:0	scb[1].uart_rts:1		cpuss.swd_clk	scb[1].spi_select0:0
P3.4		prgio[1].io[4]	tcpwm.line[2]:0		tcpwm.tr_in[6]		scb[1].spi_select1:0
P3.5		prgio[1].io[5]	tcpwm.line_compl[2]:0				scb[1].spi_select2:0
P3.6		prgio[1].io[6]	tcpwm.line[3]:0				scb[1].spi_select3:0
P3.7		prgio[1].io[7]	tcpwm.line_compl[3]:0			lpcomp.comp[1]:1	scb[2].spi_miso
P4.0	csd.vref_ext			scb[0].uart_rx:0		scb[0].i2c_scl:1	scb[0].spi_mosi:0
P4.1	csd.cshieldpads			scb[0].uart_tx:0		scb[0].i2c_sda:1	scb[0].spi_miso:0
P4.2	csd.cmodpad			scb[0].uart_cts:0		lpcomp.comp[0]:0	scb[0].spi_clk:0
P4.3	csd.csh_tank			scb[0].uart_rts:0		lpcomp.comp[1]:0	scb[0].spi_select0:0

Power

The following power system diagram shows the set of power supply pins as implemented for the PSoC 4100S. The system has one regulator in Active mode for the digital circuitry. There is no analog regulator; the analog circuits run directly from the V_{DD} input.

Figure 4. Power Supply Connections



There are two distinct modes of operation. In Mode 1, the supply voltage range is 1.8 V to 5.5 V (unregulated externally; internal regulator operational). In Mode 2, the supply range is1.8 V ±5% (externally regulated; 1.71 to 1.89, internal regulator bypassed).

Mode 1: 1.8 V to 5.5 V External Supply

In this mode, the PSoC 4100S is powered by an external power supply that can be anywhere in the range of 1.8 to 5.5 V. This range is also designed for battery-powered operation. For example, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4100S supplies the internal logic and its output is connected to the V_{CCD} pin. The VCCD pin must be bypassed to ground via an external capacitor (0.1 µF; X5R ceramic or better) and must not be connected to anything else.

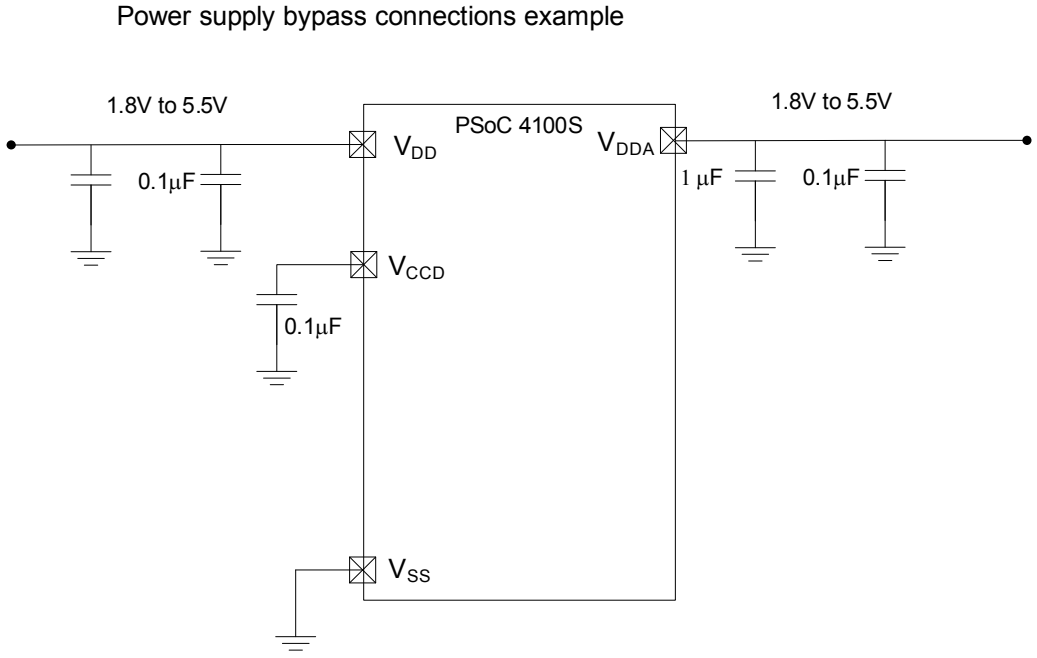
Mode 2: 1.8 V ±5% External Supply

In this mode, the PSoC 4100S is powered by an external power supply that must be within the range of 1.71 to 1.89 V; note that this range needs to include the power supply ripple too. In this mode, the VDD and VCCD pins are shorted together and bypassed. The internal regulator can be disabled in the firmware.

Bypass capacitors must be used from VDDD to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1-µF range, in parallel with a smaller capacitor (0.1 µF, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

An example of a bypass scheme is shown in the following diagram.

Figure 5. External Supply Range from 1.8 V to 5.5 V with Internal Regulator Active



Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Digital supply relative to V_{SS}	–0.5	–	6	V	–
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SS}	–0.5	–	1.95		–
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD}+0.5		–
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	–
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5		Current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–		–
BID46	LU	Pin current for latch-up	–140	–	140	mA	–

Device Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	V_{DD}	Power supply input voltage	1.8	–	5.5	V	Internally regulated supply
SID255	V_{DD}	Power supply input voltage (V_{CCD} = V_{DDD} = V_{DDA})	1.71	–	1.89		Internally unregulated supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–		–
SID55	C_{EFC}	External regulator voltage bypass	–	0.1	–	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply bypass capacitor	–	1	–		X5R ceramic or better
Active Mode, V_{DD} = 1.8 V to 5.5 V. Typical values measured at VDD = 3.3 V and 25 °C.							
SID10	I_{DD5}	Execute from flash; CPU at 6 MHz	–	1.8	2.7	mA	Max is at 85 °C and 5.5 V
SID16	I_{DD8}	Execute from flash; CPU at 24 MHz	–	3.0	4.75		Max is at 85 °C and 5.5 V
SID19	I_{DD11}	Execute from flash; CPU at 48 MHz	–	5.4	6.85		Max is at 85 °C and 5.5 V

Note
1. Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 6. GPIO AC Specifications

(Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Fast strong mode	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V≤ V_{DDD}≤ 3.3 V Fast strong mode	–	–	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Slow strong mode	–	–	7		90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO F_{OUT}; 1.71 V ≤ V_{DDD} ≤ 3.3 V Slow strong mode.	–	–	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48		90/10% V_{IO}

XRES

Table 7. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		
SID79	R_{PULLUP}	Pull-up resistor	–	60	–	kΩ	–
SID80	C_{IN}	Input capacitance	–	–	7	pF	–
SID81[5]	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Typical hysteresis is 200 mV for V_{DD} > 4.5 V
SID82	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	

Table 8. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83[5]	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–
BID194[5]	$T_{RESETWAKE}$	Wake-up time from reset release	–	–	2.7	ms	–

Note
5. Guaranteed by characterization.

Analog Peripherals

Table 9. CTBm Opamp Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
	I_{DD}	Opamp block current, External load					
SID269	I_{DD_HI}	power=hi	–	1100	1850	µA	–
SID270	I_{DD_MED}	power=med	–	550	950		–
SID271	I_{DD_LOW}	power=lo	–	150	350		–
	G_{BW}	Load = 20 pF, 0.1 mA V_{DDA} = 2.7 V					
SID272	G_{BW_HI}	power=hi	6	–	–	MHz	Input and output are 0.2 V to V_{DDA}-0.2 V
SID273	G_{BW_MED}	power=med	3	–	–		Input and output are 0.2 V to V_{DDA}-0.2 V
SID274	G_{BW_LO}	power=lo	–	1	–		Input and output are 0.2 V to V_{DDA}-0.2 V
	I_{OUT_MAX}	V_{DDA} = 2.7 V, 500 mV from rail					
SID275	$I_{OUT\_MAX\_HI}$	power=hi	10	–	–	mA	Output is 0.5 V V_{DDA}-0.5 V
SID276	$I_{OUT\_MAX\_MID}$	power=mid	10	–	–		Output is 0.5 V V_{DDA}-0.5 V
SID277	$I_{OUT\_MAX\_LO}$	power=lo	–	5	–		Output is 0.5 V V_{DDA}-0.5 V
	I_{OUT}	V_{DDA} = 1.71 V, 500 mV from rail					
SID278	$I_{OUT\_MAX\_HI}$	power=hi	4	–	–	mA	Output is 0.5 V V_{DDA}-0.5 V
SID279	$I_{OUT\_MAX\_MID}$	power=mid	4	–	–		Output is 0.5 V V_{DDA}-0.5 V
SID280	$I_{OUT\_MAX\_LO}$	power=lo	–	2	–		Output is 0.5 V V_{DDA}-0.5 V
	I_{DD_Int}	Opamp block current Internal Load					
SID269_I	$I_{DD\_HI\_Int}$	power=hi	–	1500	1700	µA	–
SID270_I	$I_{DD\_MED\_Int}$	power=med	–	700	900		–
SID271_I	$I_{DD\_LOW\_Int}$	power=lo	–	–	–		–
	G_{BW}	V_{DDA} = 2.7 V	–	–	–		–
SID272_I	$G_{BW\_HI\_Int}$	power=hi	8	–	–	MHz	Output is 0.25 V to V_{DDA}-0.25 V

Table 9. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
		General opamp specs for both internal and external modes					
SID281	V_{IN}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2	V	–
SID282	V_{CM}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2		–
	V_{OUT}	V_{DDA} = 2.7 V					
SID283	V_{OUT_1}	power=hi, Iload=10 mA	0.5	–	V_{DDA} -0.5	V	–
SID284	V_{OUT_2}	power=hi, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID285	V_{OUT_3}	power=med, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID286	V_{OUT_4}	power=lo, Iload=0.1 mA	0.2	–	V_{DDA} -0.2		–
SID288	V_{OS_TR}	Offset voltage, trimmed	–1.0	±0.5	1.0	mV	High mode, input 0 V to V_{DDA}-0.2 V
SID288A	V_{OS_TR}	Offset voltage, trimmed	–	±1	–		Medium mode, input 0 V to V_{DDA}-0.2 V
SID288B	V_{OS_TR}	Offset voltage, trimmed	–	±2	–		Low mode, input 0 V to V_{DDA}-0.2 V
SID290	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/C	High mode
SID290A	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Medium mode
SID290B	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–		Low mode
SID291	CMRR	DC	70	80	–	dB	Input is 0 V to V_{DDA}-0.2 V, Output is 0.2 V to V_{DDA}-0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	–		V_{DDD} = 3.6 V, high-power mode, input is 0.2 V to V_{DDA}-0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power=Hi	–	72	–	nV/rtHz	3
SID295	VN3	Input-referred, 10 kHz, power=Hi	–	28	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID296	VN4	Input-referred, 100 kHz, power=Hi	–	15	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID297	C_{LOAD}	Stable up to max. load. Performance specs at 50 pF.	–	–	125	pF	–
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V_{DDA} = 2.7 V	6	–	–	V/µs	–

Table 9. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID_DS_7	$G_{BW\_HI\_M1}$	Mode 1, High current	–	4	–	MHz	20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_8	$G_{BW\_MED\_M1}$	Mode 1, Medium current	–	2	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_9	$G_{BW\_LOW\_M!}$	Mode 1, Low current	–	0.5	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_10	$G_{BW\_HI\_M2}$	Mode 2, High current	–	0.5	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_11	$G_{BW\_MED\_M2}$	Mode 2, Medium current	–	0.2	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_12	$G_{BW\_Low\_M2}$	Mode 2, Low current	–	0.1	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_13	$V_{OS\_HI\_M1}$	Mode 1, High current	–	5	–	mV	With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_14	$V_{OS\_MED\_M1}$	Mode 1, Medium current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_15	$V_{OS\_LOW\_M2}$	Mode 1, Low current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_16	$V_{OS\_HI\_M2}$	Mode 2, High current	–	5	–		With trim 25 °C, 0.2V to V_{DDA}-0.2 V
SID_DS_17	$V_{OS\_MED\_M2}$	Mode 2, Medium current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_18	$V_{OS\_LOW\_M2}$	Mode 2, Low current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_19	$I_{OUT\_HI\_M!}$	Mode 1, High current	–	10	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_20	$I_{OUT\_MED\_M1}$	Mode 1, Medium current	–	10	–		Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_21	$I_{OUT\_LOW\_M1}$	Mode 1, Low current	–	4	–		Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_22	$I_{OUT\_HI\_M2}$	Mode 2, High current	–	1	–		
SID_DS_23	$I_{OU\_MED\_M2}$	Mode 2, Medium current	–	1	–		
SID_DS_24	$I_{OU\_LOW\_M2}$	Mode 2, Low current	–	0.5	–		

Note
6. Guaranteed by characterization.

CSD

Table 14. CSD and IDAC Specifications

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SYS.PER#3	VDD_RIPPLE	Max allowed ripple on power supply, DC to 10 MHz	–	–	±50	mV	V_{DD} > 2 V (with ripple), 25 °C T_A, Sensitivity = 0.1 pF
SYS.PER#16	VDD_RIPPLE_1.8	Max allowed ripple on power supply, DC to 10 MHz	–	–	±25	mV	V_{DD} > 1.75V (with ripple), 25 °C T_A, Parasitic Capacitance (C_P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	ICSD	Maximum block current	–	–	4000	µA	Maximum block current for both IDACs in dynamic (switching) mode including comparators, buffer, and reference generator.
SID.CSD#15	V_{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#15A	VREF_EXT	External Voltage reference for CSD and Comparator	0.6		V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#16	IDAC1IDD	IDAC1 (7-bits) block current	–	–	1750	µA	
SID.CSD#17	IDAC2IDD	IDAC2 (7-bits) block current	–	–	1750	µA	
SID308	VCSD	Voltage range of operation	1.71	–	5.5	V	1.8 V ±5% or 1.8 V to 5.5 V
SID308A	VCOMPIDAC	Voltage compliance range of IDAC	0.6	–	V_{DDA} –0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID309	IDAC1DNL	DNL	–1	–	1	LSB	
SID310	IDAC1INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID311	IDAC2DNL	DNL	–1	–	1	LSB	
SID312	IDAC2INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	–	–	Ratio	Capacitance range of 5 to 35 pF, 0.1-pF sensitivity. All use cases. V_{DDA} > 2 V.
SID314	IDAC1CRT1	Output current of IDAC1 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID314A	IDAC1CRT2	Output current of IDAC1(7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID314B	IDAC1CRT3	Output current of IDAC1(7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID314C	IDAC1CRT12	Output current of IDAC1 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID314D	IDAC1CRT22	Output current of IDAC1(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID314E	IDAC1CRT32	Output current of IDAC1(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315	IDAC2CRT1	Output current of IDAC2 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID315A	IDAC2CRT2	Output current of IDAC2 (7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID315B	IDAC2CRT3	Output current of IDAC2 (7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID315D	IDAC2CRT22	Output current of IDAC2(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315F	IDAC3CRT13	Output current of IDAC in 8-bit mode in low range	8	–	10.5	µA	LSB = 37.5-nA typ.

Table 14. CSD and IDAC Specifications *(continued)*

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID315G	IDAC3CRT23	Output current of IDAC in 8-bit mode in medium range	69	–	82	µA	LSB = 300-nA typ.
SID315H	IDAC3CRT33	Output current of IDAC in 8-bit mode in high range	540	–	660	µA	LSB = 2.4-µA typ.
SID320	IDACOFFSET	All zeroes input	–	–	1	LSB	Polarity set by Source or Sink. Offset is 2 LSBs for 37.5 nA/LSB mode
SID321	IDACGAIN	Full-scale error less offset	–	–	±10	%	
SID322	IDACMISMATCH1	Mismatch between IDAC1 and IDAC2 in Low mode	–	–	9.2	LSB	LSB = 37.5-nA typ.
SID322A	IDACMISMATCH2	Mismatch between IDAC1 and IDAC2 in Medium mode	–	–	5.6	LSB	LSB = 300-nA typ.
SID322B	IDACMISMATCH3	Mismatch between IDAC1 and IDAC2 in High mode	–	–	6.8	LSB	LSB = 2.4-µA typ.
SID323	IDACSET8	Settling time to 0.5 LSB for 8-bit IDAC	–	–	10	µs	Full-scale transition. No external load.
SID324	IDACSET7	Settling time to 0.5 LSB for 7-bit IDAC	–	–	10	µs	Full-scale transition. No external load.
SID325	CMOD	External modulator capacitor.	–	2.2	–	nF	5-V rating, X7R or NP0 cap.

Table 15. 10-bit CapSense ADC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SIDA94	A_RES	Resolution	–	–	10	bits	Auto-zeroing is required every millisecond
SIDA95	A_CHNLS_S	Number of channels - single ended	–	–	16		Defined by AMUX Bus.
SIDA97	A-MONO	Monotonicity	–	–	–	Yes	
SIDA98	A_GAINERR	Gain error	–	–	±2	%	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA99	A_OFFSET	Input offset voltage	–	–	3	mV	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA100	A_ISAR	Current consumption	–	–	0.25	mA	
SIDA101	A_VINS	Input voltage range - single ended	V_{SSA}	–	V_{DDA}	V	
SIDA103	A_INRES	Input resistance	–	2.2	–	KΩ	
SIDA104	A_INCAP	Input capacitance	–	20	–	pF	
SIDA106	A_PSRR	Power supply rejection ratio	–	60	–	dB	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA107	A_TACQ	Sample acquisition time	–	1	–	µs	
SIDA108	A_CONV8	Conversion time for 8-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	–	–	21.3	µs	Does not include acquisition time. Equivalent to 44.8 ksps including acquisition time.
SIDA108A	A_CONV10	Conversion time for 10-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	–	–	85.3	µs	Does not include acquisition time. Equivalent to 11.6 ksps including acquisition time.

Table 19. SPI DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID163	ISPI1	Block current consumption at 1 Mbps	–	–	360	µA	–
SID164	ISPI2	Block current consumption at 4 Mbps	–	–	560		–
SID165	ISPI3	Block current consumption at 8 Mbps	–	–	600		–

Table 20. SPI AC Specifications[8]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID166	FSPI	SPI Operating frequency (Master; 6X Oversampling)	–	–	8	MHz	SID166
Fixed SPI Master Mode AC Specifications							
SID167	TDMO	MOSI Valid after SClock driving edge	–	–	15	ns	–
SID168	TDSI	MISO Valid before SClock capturing edge	20	–	–		Full clock, late MISO sampling
SID169	THMO	Previous MOSI data hold time	0	–	–		Referred to Slave capturing edge
Fixed SPI Slave Mode AC Specifications							
SID170	TDMI	MOSI Valid before Sclock Capturing edge	40	–	–	ns	–
SID171	TDSO	MISO Valid after Sclock driving edge	–	–	42 + 3*Tcpu		$T_{CPU} = 1/F_{CPU}$
SID171A	TDSO_EXT	MISO Valid after Sclock driving edge in Ext. Clk mode	–	–	48		–
SID172	THSO	Previous MISO data hold time	0	–	–		–
SID172A	TSSELSSCK	SSEL Valid to first SCK Valid edge	–	–	100	ns	–

SWD Interface

Table 29. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID213	F_SWDCLK1	3.3 V ≤ V_{DD} ≤ 5.5 V	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	1.71 V ≤ V_{DD} ≤ 3.3 V	–	–	7		SWDCLK ≤ 1/3 CPU clock frequency
SID215[12]	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	–	–	ns	–
SID216[12]	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	–	–		–
SID217[12]	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5*T		–
SID217A[12]	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–		–

Internal Main Oscillator

Table 30. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID218	I_{IMO1}	IMO operating current at 48 MHz	–	–	250	µA	–
SID219	I_{IMO2}	IMO operating current at 24 MHz	–	–	180	µA	–

Table 31. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	$F_{IMOTOL1}$	Frequency variation at 24, 32, and 48 MHz (trimmed)	–	–	±2	%	
SID226	$T_{STARTIMO}$	IMO startup time	–	–	7	µs	–
SID228	$T_{JITRMSIMO2}$	RMS jitter at 24 MHz	–	145	–	ps	–

Internal Low-Speed Oscillator

Table 32. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231[12]	I_{ILO1}	ILO operating current	–	0.3	1.05	µA	–

Table 33. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234[12]	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID236[12]	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	–
SID237	$F_{ILOTRIM1}$	ILO frequency range	20	40	80	kHz	–

Note
12. Guaranteed by characterization.

Table 34. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID398	FWCO	Crystal Frequency	–	32.768	–	kHz	
SID399	FTOL	Frequency tolerance	–	50	250	ppm	With 20-ppm crystal
SID400	ESR	Equivalent series resistance	–	50	–	kΩ	
SID401	PD	Drive Level	–	–	1	µW	
SID402	TSTART	Startup time	–	–	500	ms	
SID403	CL	Crystal Load Capacitance	6	–	12.5	pF	
SID404	C0	Crystal Shunt Capacitance	–	1.35	–	pF	
SID405	IWCO1	Operating Current (high power mode)	–	–	8	uA	
SID406	IWCO2	Operating Current (low power mode)	–	–	1	uA	

Table 35. External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID305[13]	ExtClkFreq	External clock input frequency	0	–	48	MHz	–
SID306[13]	ExtClkDuty	Duty cycle; measured at $V_{DD/2}$	45	–	55	%	–

Table 36. Block Specs

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID262[13]	$T_{CLKSWITCH}$	System clock source switching time	3	–	4	Periods	–

Table 37. Smart I/O Pass-through Time (Delay in Bypass Mode)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID252	PRG_BYPASS	Max delay added by Smart I/O in bypass mode	–	–	1.6	ns	

Note
13. Guaranteed by characterization.

Ordering Information

The marketing part numbers for the PSoC 4100S family are listed in the following table.

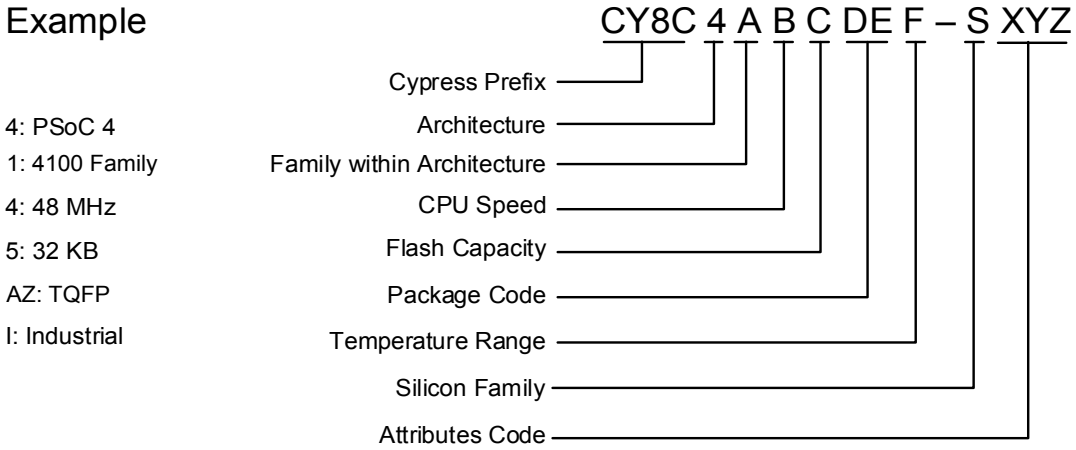
Category	MPN	Features													Package				
		Max CPU Speed (MHz)	Flash (KB)	SRAM (KB)	Opamp (CTBm)	CSD	10-bit CSD ADC	12-bit SAR ADC	ADC Sample Rate	LP Comparators	TCPWM Blocks	SCB Blocks	Smart I/Os	GPIO	35-WLCSP (0.35mm pitch)	32-QFN	40-QFN	48-TQFP	44-TQFP
4124	CY8C4124FNI-S403	24	16	4	2	0	1	0		2	5	2	8	31	X				
	CY8C4124FNI-S413	24	16	4	2	1	1	0		2	5	2	16	31	X				
	CY8C4124LQI-S412	24	16	4	2	1	1	0		2	5	2	16	27		X			
	CY8C4124LQI-S413	24	16	4	2	1	1	0		2	5	2	16	34			X		
	CY8C4124AZI-S413	24	16	4	2	1	1	0		2	5	2	16	36				X	
	CY8C4124FNI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	31	X				
	CY8C4124LQI-S432	24	16	4	2	1	1	1	806 ksps	2	5	2	16	27		X			
	CY8C4124LQI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	34			X		
	CY8C4124AZI-S433	24	16	4	2	1	1	1	806 ksps	2	5	2	16	36				X	
4125	CY8C4125FNI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	31	X				
	CY8C4125LQI-S422	24	32	4	2	0	1	1	806 ksps	2	5	2	16	27		X			
	CY8C4125LQI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	34			X		
	CY8C4125AZI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	36				X	
	CY8C4125AXI-S423	24	32	4	2	0	1	1	806 ksps	2	5	2	16	36					X
	CY8C4125FNI-S413	24	32	4	2	1	1	0		2	5	2	16	31	X				
	CY8C4125LQI-S412	24	32	4	2	1	1	0		2	5	2	16	27		X			
	CY8C4125LQI-S413	24	32	4	2	1	1	0		2	5	2	16	34			X		
	CY8C4125AZI-S413	24	32	4	2	1	1	0		2	5	2	16	36				X	
	CY8C4125FNI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	31	X				
	CY8C4125LQI-S432	24	32	4	2	1	1	1	806 ksps	2	5	2	16	27		X			
	CY8C4125LQI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	34			X		
	CY8C4125AZI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	36				X	
	CY8C4125AXI-S433	24	32	4	2	1	1	1	806 ksps	2	5	2	16	36					X
4126	CY8C4126AZI-S423	24	64	8	2	0	1	1	806 ksps	2	5	3	16	36				X	
	CY8C4126AXI-S423	24	64	8	2	0	1	1	806 ksps	2	5	3	16	36					X
	CY8C4126AZI-S433	24	64	8	2	1	1	1	806 ksps	2	5	3	16	36				X	
	CY8C4126AXI-S433	24	64	8	2	1	1	1	806 ksps	2	5	3	16	36					X
4145	CY8C4145AZI-S423	48	32	4	2	0	1	1	1 Msps	2	5	2	16	36				X	
	CY8C4145AXI-S423	48	32	4	2	0	1	1	1 Msps	2	5	2	16	36					X
	CY8C4145AXI-S433	48	32	4	2	1	1	1	1 Msps	2	5	2	16	36					X
4146	CY8C4146FNI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	31	X				
	CY8C4146LQI-S422	48	64	8	2	0	1	1	1 Msps	2	5	3	16	27		X			
	CY8C4146LQI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	34			X		
	CY8C4146AZI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	36				X	
	CY8C4146AXI-S423	48	64	8	2	0	1	1	1 Msps	2	5	3	16	36					X
	CY8C4146FNI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	31	X				
	CY8C4146LQI-S432	48	64	8	2	1	1	1	1 Msps	2	5	3	16	27		X			
	CY8C4146LQI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	34			X		
	CY8C4146AZI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	36				X	
	CY8C4146AXI-S433	48	64	8	2	1	1	1	1 Msps	2	5	3	16	36					X

The nomenclature used in the preceding table is based on the following part numbering convention:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family	1	4100 Family
B	CPU Speed	2	24 MHz
		4	48 MHz
C	Flash Capacity	4	16 KB
		5	32 KB
		6	64 KB
		7	128 KB
DE	Package Code	AX	TQFP (0.8mm pitch)
		AZ	TQFP (0.5mm pitch)
		LQ	QFN
		PV	SSOP
		FN	CSP
F	Temperature Range	I	Industrial
S	Silicon Family	S	PSoC 4A-S1, PSoC 4A-S2
		M	PSoC 4A-M
		L	PSoC 4A-L
		BL	PSoC 4A-BLE
XYZ	Attributes Code	000-999	Code of feature set in the specific family

The following is an example of a part number:

Example



Packaging

The PSoC 4100S will be offered in 48-pin TQFP, 44-pin TQFP, 40-pin QFN, 32-pin QFN, and 35-ball WLCSP packages. Package dimensions and Cypress drawing numbers are in the following table.

Table 38. Package List

Spec ID#	Package	Description	Package Dwg
BID20	48-pin TQFP	7 × 7 × 1.4-mm height with 0.5-mm pitch	51-85135
BID20A	44-pin TQFP	10 × 10 × 1.6-mm height with 0.8-mm pitch	51-85064
BID27	40-pin QFN	6 × 6 × 0.6-mm height with 0.5-mm pitch	001-80659
BID34A	32-pin QFN	5 × 5 × 0.6-mm height with 0.5-mm pitch	001-42168
BID34D	35-ball WLCSP	2.6 × 2.1 × 0.48-mm height with 0.35-mm pitch	002-09958

Table 39. Package Thermal Characteristics

Parameter	Description	Package	Min	Typ	Max	Units
T_A	Operating Ambient temperature		–40	25	85	°C
T_J	Operating junction temperature		–40	–	100	°C
T_{JA}	Package θ_{JA}	48-pin TQFP	–	74.8	–	°C/Watt
T_{JC}	Package θ_{JC}	48-pin TQFP	–	35.7	–	°C/Watt
T_{JA}	Package θ_{JA}	44-pin TQFP	–	57.2	–	°C/Watt
T_{JC}	Package θ_{JC}	44-pin TQFP	–	17.5	–	°C/Watt
T_{JA}	Package θ_{JA}	40-pin QFN	–	17.8	–	°C/Watt
T_{JC}	Package θ_{JC}	40-pin QFN	–	2.8	–	°C/Watt
T_{JA}	Package θ_{JA}	32-pin QFN	–	19.9	–	°C/Watt
T_{JC}	Package θ_{JC}	32-pin QFN	–	4.3	–	°C/Watt
T_{JA}	Package θ_{JA}	35-ball WLCSP	–	43	–	°C/Watt
T_{JC}	Package θ_{JC}	35-ball WLCSP	–	0.3	–	°C/Watt

Table 40. Solder Reflow Peak Temperature

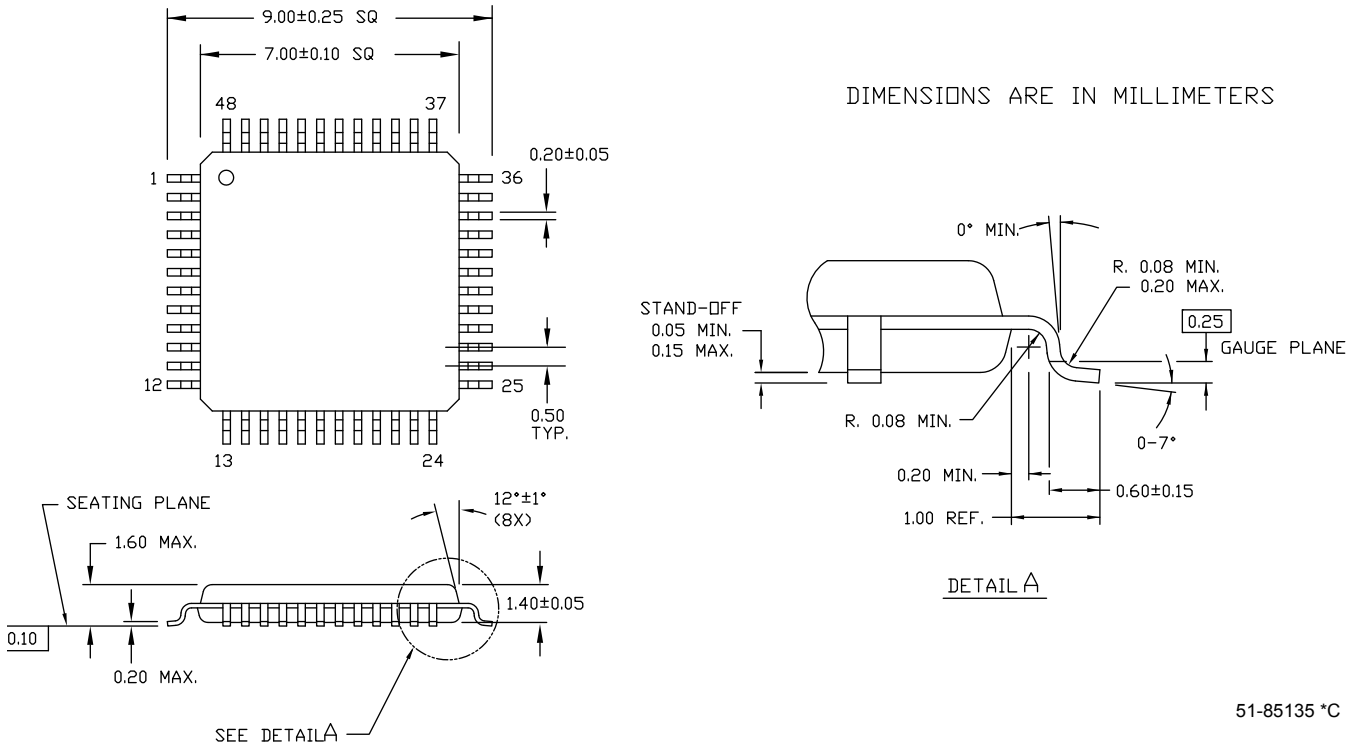
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All	260 °C	30 seconds

Table 41. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-020

Package	MSL
All except WLCSP	MSL 3
35-ball WLCSP	MSL 1

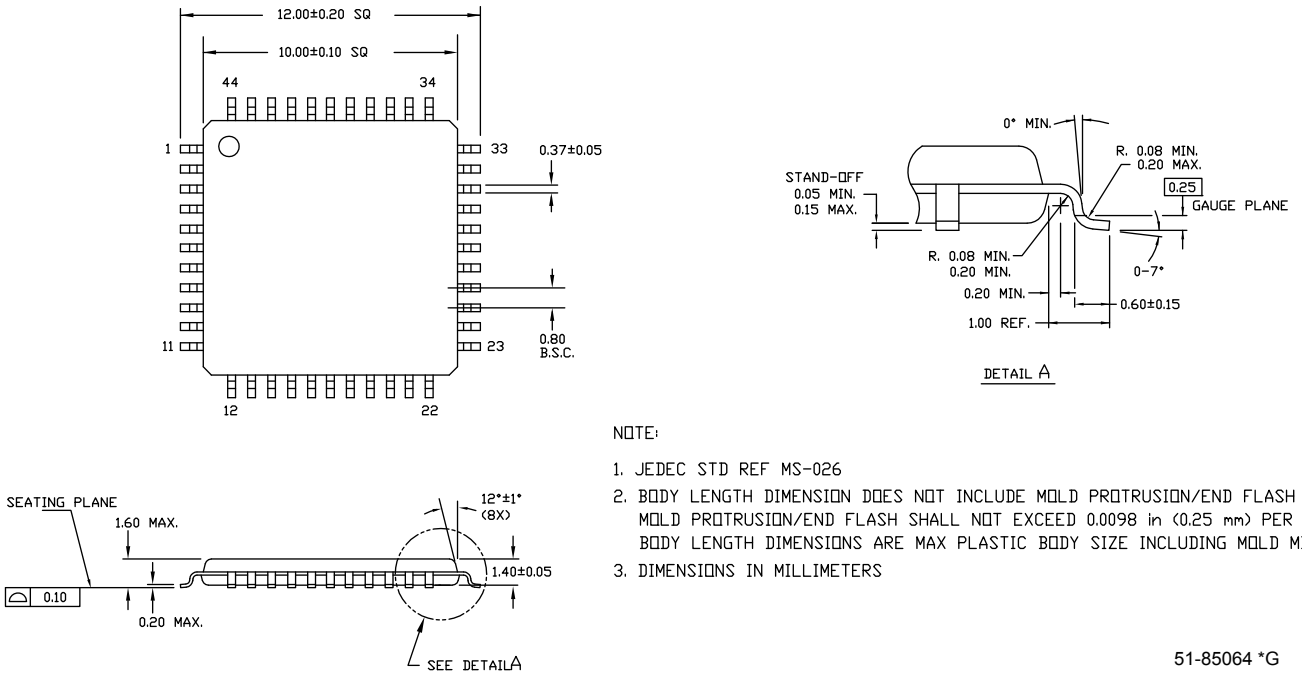
Package Diagrams

Figure 6. 48-pin TQFP Package Outline



51-85135 *C

Figure 7. 44-pin TQFP Package Outline

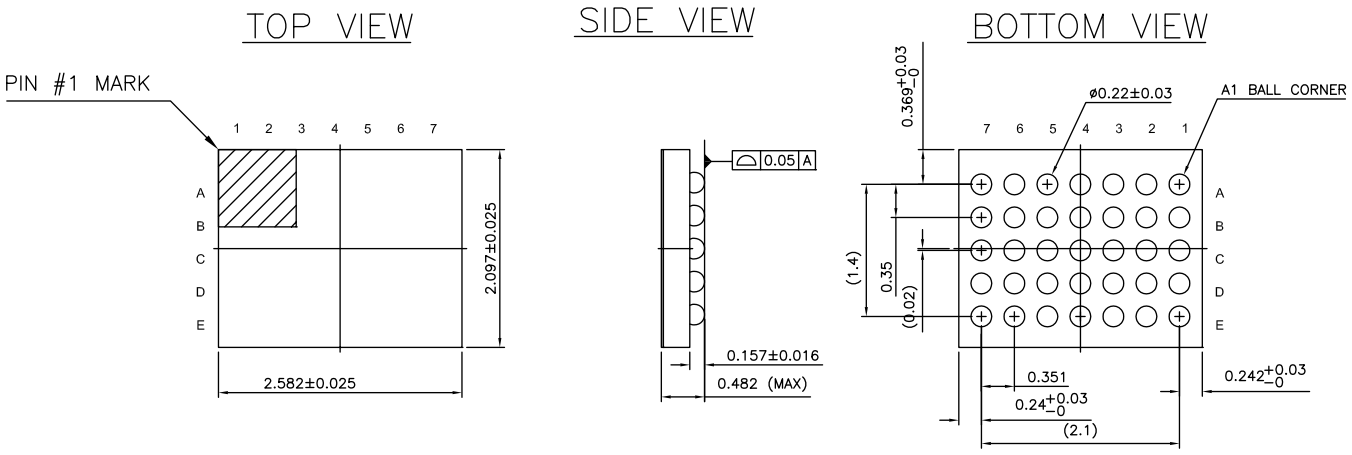


NOTE:

1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
   BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85064 *G

Figure 10. 35-Ball WLCSP Package Outline



ALL DIMENSIONS ARE IN MM
JEDEC Publication 95; Design Guide 4.18

002-09958 *C